

Effective medium theory for the electrical conductivity of random metallic nanowire networks

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Interest in studying the conductive properties of networks made from randomly distributed nanowires is due to their numerous technological applications. Although the sheet resistance of such networks can be calculated directly, the calculations require many characteristics of the system (distributions of lengths, diameters and resistances of nanowires, distribution of junction resistance), the measurement of which is difficult. Furthermore, such calculations can hardly offer an analytical dependence of the sheet resistance on the basic physical parameters of the systems under consideration. Although various theoretical approaches offer such analytical dependencies, they are often based on more or less reasonable assumptions rather than rigorously proven statements. Here, we offer an approach based on Foster's theorem to reveal a dependence of the sheet resistance of dense nanowire networks on the main parameters of such networks. This theorem offers an additional perspective on the effective medium theory and extends our insight.

I. INTRODUCTION

The effective medium theory (EMT) has been proposed by Bruggeman [1] to calculate physical constants of heterogeneous media such as dielectric constants and conductivities of composite media made of isotropic substances. EMT has as well been adapted to random resistor networks (RRNs), viz, regular networks with randomly distributed branch conductivities [2–5]. For regular RRNs, the idea is to replace a network having random values of branch conductivity with a network of the same structure having identical values of all edge conductivities. In all those cases [2–5], derivations were based on the symmetry of the networks under consideration. However, symmetry is not a necessary requirement, the results are also valid for regular networks, i.e., networks, in which all nodes have the same valence (degree). The same results can be obtained on the basis of the Foster's theorem [6]. Marchant [7] has demonstrated applications of the Foster's theorem to some particular resistor networks, viz., to regular networks having randomly distributed branch admittances, to irregular networks having identical branch admittances, and to irregular networks having randomly distributed branch admittances. Unfortunately, in the latter case, progress is rather modest as compared to the first two cases. For a regular network (deg $V = z$ for each node) with identical branch conductances $g = g_m$,

$$\frac{g_m}{g_m + G'} = \frac{2}{z}, \quad (1)$$

where G' is the conductance between any two nearest nodes of the network when g is disconnected. Then, all

G' have the same value

$$G' = g_m \left(\frac{z}{2} - 1 \right). \quad (2)$$

The application of EMT to regular networks is equivalent to a replacement of the distribution of g , by a unique value g_m obtained in an 'effective network' of the *same structure*, filled with identical conductances g_m and given by (2), which leads to the approximation [7] (cf. [3])

$$\int f_G(g) \frac{g_m - g}{g + g_m \left(\frac{z}{2} - 1 \right)} dg \approx 0. \quad (3)$$

Besides, Marchant [7] explained the source of errors in the EMT predictions. Clerc *et al.* [8] presented a review of works devoted to electrical conductivity of binary disordered systems.

Numerous technological applications of transparent conductive films (TCFs) based on randomly deposited metallic nanowires (random nanowire networks, RNNs) motivate interest in studying the properties of such random networks [9–12]. Table I presents average length, $\langle l_0 \rangle$, and diameter, $\langle d \rangle$, of silver nanowires (AgNWs) used to produce TCFs. Deposited mass of AgNWs per unit area (areal mass density, amd) is also presented in Table I. In modeling, it is customary to use the number density, i.e., the number of particles, N , per unit area, A ,

$$n = \frac{N}{A} \quad (4)$$

and it is convenient to take the length of the particle as the unit of length, i.e., use nl_0^2 .

Table I suggests that the typical number density of nanowires nl_0^2 is few tens, while the maximal value in the exceptional cases may reach several hundreds. Obviously, that the minimal number density of nanowires has to correspond to the percolation threshold, since otherwise the system is insulating.

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TABLE I. Some characteristics of TCFs produced of AgNWs.

Refs.	$\langle l_0 \rangle, \mu\text{m}$	$\langle d \rangle, \text{nm}$	amd, mg/m^2
	20.4	26	20–50
	13.6	45	20–120
Lagrange <i>et al.</i> [13]	7.6	55	50–150
	42.9	117	20–220
	32.0	138	50–300
Bardet <i>et al.</i> [14]	8 ± 3	79 ± 10	25–250
	11 ± 5.8	119 ± 23	
Sannicolo <i>et al.</i> [10]	~ 10	20–150	40–200
De <i>et al.</i> [15]	6.6	84	28–780
Celle <i>et al.</i> [16]	2–25	40–80	35
Nian <i>et al.</i> [17]	15	35	3.1–16
Göbelt <i>et al.</i> [18]	5.81	118	331
Yu <i>et al.</i> [19]	80	88	94–366.2
Milano <i>et al.</i> [20]	35	115	60–181

O’Callaghan *et al.* [21] studied the random nanowire networks (RNNs) accounting for both wire resistance and the contact resistance (so-called multinodal representation [22]). They applied the EMT to find the dependency of the sheet resistance of transparent conductive films (TCFs) on the concentration of nanowires. Several assumptions were stated and used in their consideration, viz, (i) dense RNNs can be considered as square lattices with conductive edges, (ii) optimal path between the two opposite border of the RNNs can be obtained using some ideas related to small-world networks, (iii) lengths of wire segments correspond to Poisson distribution, (iv) conductivities of contacts and wire segments are independently distributed.

Actually, the Poisson distribution describes the number of contacts per wire, while lengths of wire segments correspond to an exponential distribution [23]. However, O’Callaghan *et al.* [21] replaced the actual length distribution by average value of the segment length.

O’Callaghan *et al.* [21] demonstrated that, for both RNNs and a square lattice, dependencies of the two-point resistances on the distance between nodes are similar. This observation was used to replace an RNN by a square lattice [21].

Zeng *et al.* [24] proposed another way how to correlate site percolation on a square lattice to disordered nanowire networks (DNNs) and compared an EMT and an effective path theory (EPT) [25].

Our goal is utilisation of the EMT with minimal and rigorously reasonable assumptions to find the dependence of the electrical conductivity of RNNs on the main physical parameters. The rest of the paper is constructed as follows. Section II provides necessary information and describes some technical details of simulation. Section III presents the analytical approach, together with our main findings. Section IV summarizes the main results.

II. METHODS

Since the typical aspect ratio, i.e., the ratio of nanowire length to its diameter is 100 of order of magnitude, the nanowires in simulations are often represented as zero-width conductive segments (sticks) [21, 23, 26–28]. We use the same approach. Note that although model of zero-width sticks is widely used, it has some obvious limitations. Since our focus are nanowires with large but finite aspect ratio, in our 2D model, the distance between the two nearest contacts has to be larger than the nanowire diameter (cf. Daniels and Brown [29]).

Let there be N zero-width line segments (sticks) of equal length l_0 . These sticks are deposited in such a way that coordinates of their centers are independent and identically distributed (i.i.d.) within the domain $L \times L$ with periodic boundary conditions (PBCs), while their orientations are equiprobable. The electrical resistance of each stick is R_w , while the electrical resistance of each contact (junction) between segments is R_j . In such a way, a RNN is mapped to a RRN.

Very important that obtained RRN is not a regular network despite $\langle z \rangle$ tends to 3 when RNNs under consideration are dense. We should emphasize that, in Ref. 21, before EMT was applicable to RNNs, the real structure of the RRN under consideration was replaced by a square lattice. That replacement of the network structure rather than use a network of the same structure seems to contradict the basic idea of EMT.

However, an RNN can be turned out into a regular network by applying a simple transformation. Let us mentally connect both ends of one nanowire. In order to preserve the electrical conductivity of the entire RNN, zero electrical conductivity should be assigned to this newly created edge connecting the extreme contacts on the nanowire, since the end segments of the nanowire do not participate in electrical conductivity. By applying such a closure to all nanowires, we obtain a 3-regular network, which has the same electrical conductivity as the original RNN (Fig. 1).

The average number of contacts (junctions) per a nanowire is

$$\langle k \rangle = \frac{2}{\pi} n l_0^2, \quad (5)$$

(see, e.g., Refs. 28 and 30). Associating a resistor, R_j , with each junction between the nanowires, we have $N n l_0^2 / \pi$ such resistors. Besides, there are N resistor having zero conductivity, which correspond to the imaginary closed termini of nanowires.

Since there are on average $\langle k \rangle$ contacts on a nanowire, the average number of internal segments into which the nanowire is divided is $\langle k \rangle - 1$. The total number of internal segments in the entire system is $N(\langle k \rangle - 1)$. When the electrical resistance of a nanowire of length l_0 is R_w , then the resistance of a nanowire segment, l , between nearest junctions is $R_w l / l_0$. The corresponding number of such

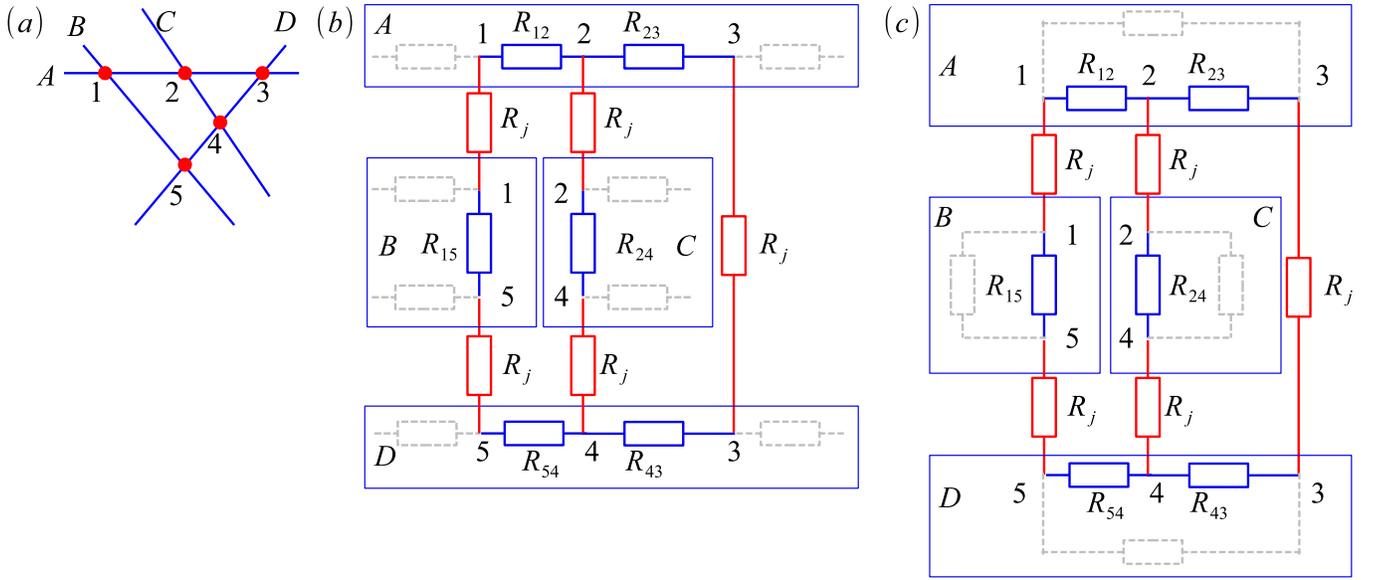


FIG. 1. (a) Example of a small nanowire network. (b) Corresponding irregular random resistor network. (c) An equivalent 3-regular random resistor network.

edges in the network is

$$N(\langle k \rangle - 1) = N \left(\frac{2}{\pi} n l_0^2 - 1 \right). \quad (6)$$

The total number of edges in the RNN is

$$\frac{N}{\pi} n l_0^2 + N \left(\frac{2}{\pi} n l_0^2 - 1 \right) + N = \frac{3}{2} \langle k \rangle N. \quad (7)$$

A fraction of edges having the resistance R_j is $1/3$. A fraction of edges having the resistance $R_w l/l_0$ is

$$\frac{2}{3} \left(1 - \frac{1}{\langle k \rangle} \right) = \frac{2}{3} - \frac{\pi}{3 n l_0^2}. \quad (8)$$

A fraction of edges having the infinite large resistance is

$$\frac{2}{3 \langle k \rangle} = \frac{\pi}{3 n l_0^2}. \quad (9)$$

The conductance PDF in the RNN is

$$f_G(g) = \frac{1}{3} f_G^{(1)}(g) + \frac{\pi}{3 n l_0^2} f_G^{(2)}(g) + \left(\frac{2}{3} - \frac{\pi}{3 n l_0^2} \right) f_G^{(3)}(g), \quad (10)$$

where $f_G^{(1)}(g) = \delta(g - R_j^{-1})$ is the PDF of edges, corresponding to junctions, $f_G^{(2)}(g) = \delta(g)$ is the PDF of imaginary nanowire segments connecting end junctions at the nanowire. Here, $\delta(x)$ means the Dirac delta function. $f_G^{(3)}(g)$ is the PDF of nanowire segments between nearest junctions. The conductance of any edge (segment) is inversely proportional to its length, viz., $g(l) = l_0/(lR_w)$, where l is the segment length.

Since, when the number density of sticks is large enough, the number of contacts on a stick obeys a Poisson distribution, lengths of segments between two nearest contacts are expected to obey an exponential distribution with the mean $\langle l \rangle$ [23]

$$f_L(l; \langle l \rangle) = \frac{1}{\langle l \rangle} \exp \left(-\frac{l}{\langle l \rangle} \right), \quad (11)$$

where

$$\langle l \rangle = \frac{l_0}{\langle k \rangle} = \frac{\pi}{2 n l_0}. \quad (12)$$

Then, $f_G^{(3)}(g)$ can be deduced from (11) as follows

$$f_G^{(3)}(g) = \frac{l_0}{R_w g^2} f_L \left(\frac{l_0}{R_w g}; \langle l \rangle \right). \quad (13)$$

Hence,

$$f_G^{(3)}(g) = \frac{2 n l_0^2}{\pi R_w g^2} \exp \left(-\frac{2 n l_0^2}{\pi R_w g} \right). \quad (14)$$

III. RESULTS

A. Both junction resistances and wire resistance are accounted for

Since the effective network under consideration is a 3-regular network with randomly distributed resistances of edges, hence, according to Ref. 7, (3) is as well valid in this case, if PDF $f_G(g)$ corresponds the above described

distribution

$$f_G(g) = \frac{1}{3}\delta(g - R_j^{-1}) + \frac{\pi}{3nl_0^2}\delta(g) + \left(\frac{2}{3} - \frac{\pi}{3nl_0^2}\right) \frac{2nl_0^2}{\pi R_w g^2} \exp\left(-\frac{2nl_0^2}{\pi R_w g}\right). \quad (15)$$

Since in our case $\deg V = 3$,

$$G' = \frac{gm}{2} \quad (16)$$

(cf. Joy and Strieder [5], Tarasevich *et al.* [31]). For a regular network with different branch conductances

$$\left\langle \frac{g}{g + G'} \right\rangle = \frac{2}{\deg V}. \quad (17)$$

Then, the effective medium conductance, g_m , can be found by subtracting (1) and (17)

$$\int_{g_0}^{\infty} f_G(g) \frac{g_m - g}{g_m/2 + g} dg = 0. \quad (18)$$

Then,

$$\left(2 - \frac{\pi}{nl_0^2}\right) \int_0^{\infty} \frac{2nl_0^2}{\pi R_w g^2} \exp\left(-\frac{2nl_0^2}{\pi R_w g}\right) \frac{g_m - g}{g_m + 2g} dg + \frac{g_m R_j - 1}{g_m R_j + 2} + \frac{\pi}{nl_0^2} = 0. \quad (19)$$

Here, we extended an integration limit, accounting for that the PDF decreasing very fast when the number density of wires is large.

$$\left(2 - \frac{\pi}{nl_0^2}\right) \int_0^{\infty} \frac{2nl_0^2}{\pi R_w g} \exp\left(-\frac{2nl_0^2}{\pi R_w g}\right) \frac{dg}{g_m + 2g} = \frac{g_m R_j + 1}{g_m R_j + 2}. \quad (20)$$

Using the exponential integral, $E_1(x)$, we get

$$2 \frac{2nl_0^2}{\pi R_w g_m} \text{Ei}_1\left(2 \frac{2nl_0^2}{\pi R_w g_m}\right) \exp\left(2 \frac{2nl_0^2}{\pi R_w g_m}\right) = \frac{g_m R_j + 1}{g_m R_j + 2} \left(1 - \frac{\pi}{2nl_0^2}\right)^{-1}. \quad (21)$$

When $R_j = 0$, numerical solution of (21) gives

$$g_m R_w \approx 3.275 \frac{2nl_0^2}{\pi}, \quad (22)$$

hence, $g_m R_w = 2.08nl_0^2$.

In the common case, (21) was found for different values of R_j . Figure 2 presents dependence of the effective conductivity, g_m , on the quantity $4nl_0^2/(\pi R_w)$.

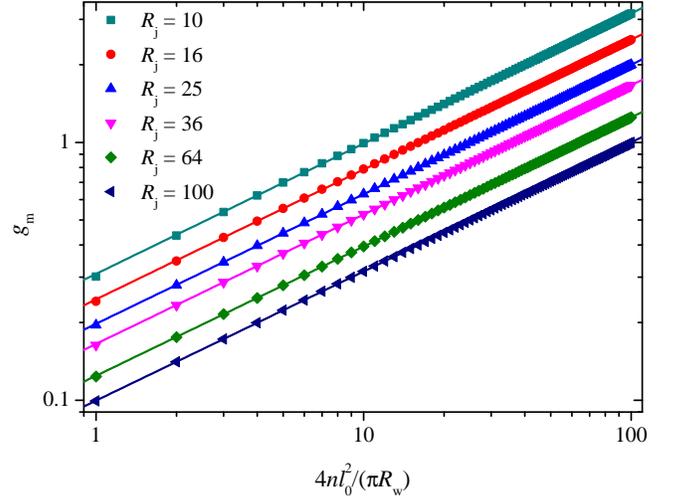


FIG. 2. Dependence of the effective conductivity, g_m , on the effective concentration of nanowires for different values of the junction resistance, R_j . Lines correspond to the least squares fits.

Table II presents results of the least squares fitting

$$\log_{10} g_m = A \log_{10} \frac{4nl_0^2}{\pi R_w} + B. \quad (23)$$

These results suggest that, for large values of R_j , the effective conductive can be written as follows

$$g_m = \sqrt{\frac{4nl_0^2}{\pi R_j R_w}}. \quad (24)$$

TABLE II. Least squares fit

R_j	A	B	10^{-2B}
1	0.512	-0.026	1.13
2	0.510	-0.171	2.2
10	0.505	-0.510	10.5
16	0.504	-0.609	16.5
25	0.503	-0.704	25.6
36	0.502	-0.782	36.6
64	0.501	-0.905	64.6
100	0.501	-1.001	100.6

An assumption that the wire resistance is negligible as compared to the junction resistance is widely used [22, 32–34]. This assumptions is quite natural for dense nanowire networks. When $R_w = 0$, $f_G^{(3)}(g) = 0$, thus, (19) turns out in

$$\frac{g_m R_j - 1}{g_m R_j + 2} + \frac{\pi}{nl_0^2} = 0. \quad (25)$$

Solution of this equation is

$$g_m R_j = \frac{nl_0^2 - 2\pi}{nl_0^2 + \pi}. \quad (26)$$

B. Seamless networks

When only the wire resistances are accounted for, the RNN is a planar network, which tends to a 4-regular network as the number density of wires increases, while the resistances of edges are random variables which values are proportional to edge lengths (11). Again, connecting both dead-ends of each nanowire, we got a 4-regular network, in which N resistors have infinite large resistance, while $N(\frac{2}{\pi}nl_0^2 - 1)$ resistors have the resistance $R_w l/l_0$.

$$\left(1 - \frac{\pi}{2nl_0^2}\right) \int_0^\infty \frac{2nl_0^2}{\pi R_w g^2} \exp\left(-\frac{2nl_0^2}{\pi R_w g}\right) \frac{g_m - g}{g_m + g} dg + \frac{\pi}{2nl_0^2} \int_0^\infty \delta(g) \frac{g_m - g}{g_m + g} dg = 0. \quad (27)$$

Integration leads to the following equation

$$\frac{2nl_0^2}{\pi R_w g_m} E_1\left(\frac{2nl_0^2}{\pi R_w g_m}\right) \exp\left(\frac{2nl_0^2}{\pi R_w g_m}\right) = \frac{1}{2} \left(1 - \frac{\pi}{2nl_0^2}\right)^{-1}, \quad (28)$$

which solution is

$$g_m R_w \approx 1.637 \frac{2nl_0^2}{\pi}, \quad (29)$$

i.e., $g_m R_w \approx 1.04nl_0^2$.

Note that the obtained result is valid for *any* 4-regular infinite graph, e.g., square lattice, kagome lattice, rhombitrihexagonal tiling of the Euclidean plane (3.4.6.4), etc. Although all these examples are related to planar graphs, planarity is not a necessary requirement. However, for any particular 4-regular graph, a dependency of the sheet resistance on the edge conductance is individual. Thus, for the square lattice, $R_\square = g_m^{-1}$, while, for the kagome lattice, $R_\square = 2(g_m\sqrt{3})^{-1}$. The problem is, the network under consideration is a random graph; although its edge conductance is now known, we cannot still find its sheet resistance.

To check the obtained value of the effective conductance, we used a computational test. A square lattice and a kagome lattice are instances of a 4-regular networks. In a bus-bar geometry, we calculated the conductivities of these two lattices ($L = 32, 64$, and 128) with random values of the edge conductances according to PDF (13) with $g_0 = 1$, $l_0 = 1$. The results were averaged over 10 independent runs for each value of $\langle l \rangle$. Bearing in mind RNNs, we presented in Fig. 3 the electrical conductance of the lattices against the number density of edges rather than $\langle l \rangle$. The least squares fit (LSF) suggests that the conductance is proportional to $1.037n$ in the case of a square lattice. Since in a bus-bar geometry, the resistance of a square resistor network $L \times L$ equals a resistance of one branch, in fact, Fig. 3 evidenced that the

electrical conductance of random square lattice is equal to the electrical conductance of square lattice with identical conductivity of each edge 1.04. In the case of a kagome lattice, LSF evidenced that the slope is 0.899, while the theoretical prediction suggests 0.901. We consider this as a confirmation of obtained value the effective conductance g_m .

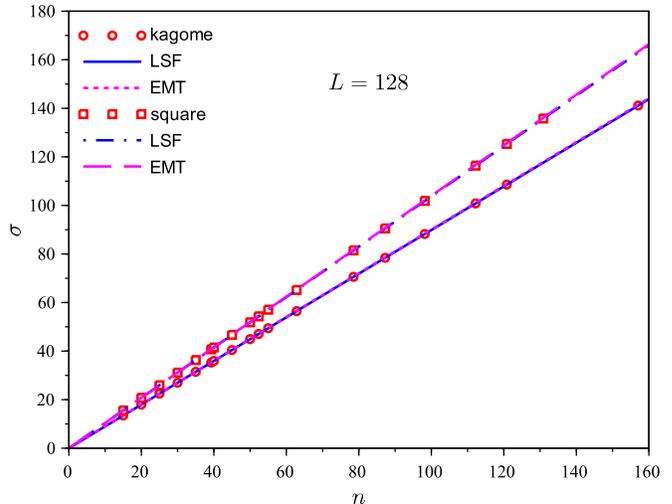


FIG. 3. Dependencies of the electrical conductance on the number density edges for a square lattice and a kagome lattice of linear size $L = 128$ and randomly distributed values of the edge conductances according to (13). Results are averaged over 10 independent runs.

Figure 4 compares the electrical conductivity of RNNs obtained using the direct computations (circles) and EMT (squares). In the latter case, all edge conductivities were set according to obtained value of g_m . The EMT gives about twice larger conductivity as compared to direct computations. Since EMT have demonstrated an excellent agreement for regular lattices (square and kagome), we can see only one reason of the discrepancy in the case of RRN. While square lattice and kagome lattice are *strictly* 4-regular, the RRN is *almost* 4-regular, i.e., dead-ends are crucial. In other words, the EMT should be applied only to the equivalent RNNs which correspond to RNNs with closed termini of nanowires.

IV. CONCLUSION

Using Foster's theorem along with rigorously reasonable assumptions, we found the dependence of the effective electrical conductivity of the edges of random nanowire networks on the main physical parameters. We demonstrated that a direct application of the effective medium theory to the random nanowire networks leads to a significant overestimate of the electrical conductance since such networks are not regular networks. An equivalent random resistor network should be used instead.

Although the EMT allows to find edge conductances

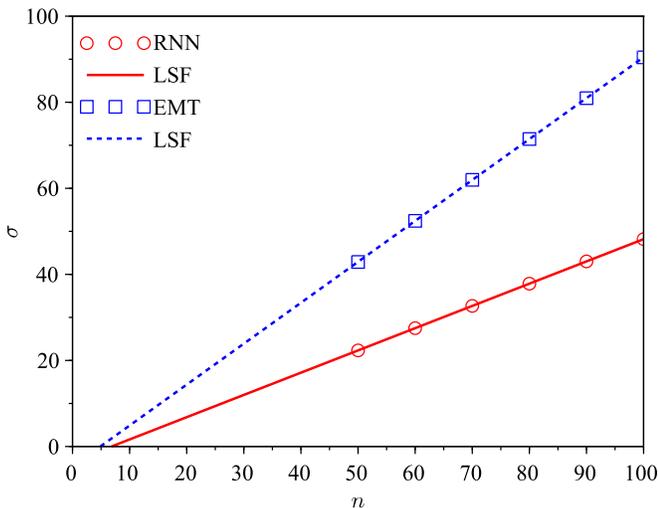


FIG. 4. Dependencies of the electrical conductance on the number density of wires for a RNN of linear size $L = 32$. Results are averaged over 10 independent runs.

to replace a regular random resistor network by a resistor network of the same structure and identical resistances of

all its branches, this cannot assist in finding of the sheet resistance unless the case networks having a translational symmetry, e.g., square, honeycomb, kagome, etc. Otherwise, different tricks should be used to map the network under consideration to a square lattice [21, 24, 25]. These tricks can hardly be considered as well founded.

Jagota and Scheinfeld [33] proposed an approximate analytical model for sheet conductivity of random nanowire networks. They accounted only for junction resistances and used an averaged Laplace matrix to find the electrical conductivity. However, the proposed approach seems to be applicable to any regular network with identical branch resistances, i.e., to those networks which are obtained after the replacement of all all branch resistances to g_m .

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